



Excellence in Electronics

TYPE 1N66

(CK705)

The 1N66 is a hermetically sealed point contact germanium diode designed for use in general purpose rectifier applications and gate leg or buffer circuits in computers. The 1N66 is particularly applicable where medium back resistance, small size, absence of heater voltage, low shunt capacitance and resistance to changes in humidity and temperature* are important. Operable at temperatures up to 100°C, it can be heated as high as 125°C with no irreversible change in characteristics. Each diode is dynamically tested for hysteresis, drift, and flutter. The 1N66 has extremely uniform electrical characteristics and reliable mechanical stability.

MECHANICAL DATA

TERMINALS: Dumet wire, Tinned to within 1/8" of barrel Diameter: 0.017" max. Length: 1" min.

TERMINAL CONNECTIONS: White Band at Cathode Terminal

MOUNTING POSITION: Any

PLUG - IN EQUIVALENT: Available as 1N66-P

ELECTRICAL DATA

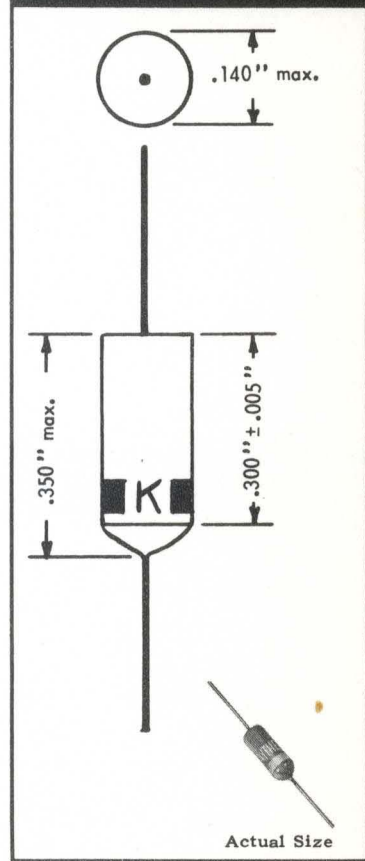
RATINGS - ABSOLUTE MAXIMUM VALUES: (at 25°C)

Inverse Voltage	60 volts
Average Rectified Current	50 ma.
Peak Rectified Current	150 ma.
Surge Current (for 1 sec.)	500 ma.
Ambient Temperature Range	- 50 to + 100 °C
Dissipations at:	
25°C	80 mw.
50°C	65 mw.
75°C	50 mw.
100°C	30 mw.

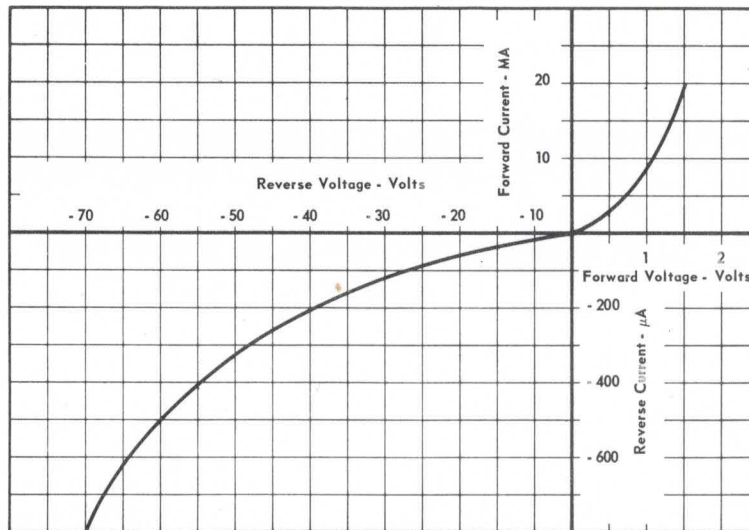
CHARACTERISTICS: (at 25°C)

Maximum Inverse Current at - 10 volts	50 µa.
Maximum Inverse Current at - 50 volts	800 µa.
Minimum Forward Current at + 1 volt	5.0 ma.
Shunt Capacitance	1.0 µmfd.
Minimum Reverse Voltage for Zero Dynamic Resistance	70 volts

* Each diode receives repeated humidity cycling, and additional temperature cycling ranging from -25°C to 130°C.



TYPICAL STATIC CHARACTERISTICS (at 25°C)



Tentative Data

RAYTHEON MANUFACTURING COMPANY

RECEIVING AND CATHODE RAY TUBE OPERATIONS